查询"28K3708HippireD EFFECT TRANSISTOR SILICON N CHANNEL JUNCTION TYPE

# 2 S K 3 7 0

FOR LOW NOISE AUDIO AMPLIFIER APPLICATIONS

 Suitable for Use as First Stage for Equalizer and MC Head Amplifiers.

• High  $|Y_{fs}| : |Y_{fs}| = 22ms (Typ.) (V_{DS} = 10V, V_{GS} = 0, I_{DSS} = 3mA)$ 

● High Breakdown Voltage: VGDS = -40V

• High Input Impedance :  $I_{GSS} = -1nA \text{ (Max.) (V}_{GS} = -30V)$ 

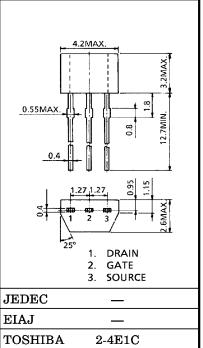
• Complementary to 2SJ108

• Small Package

#### MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Gate-Drain Voltage	$v_{GDS}$	-40	V
Gate Current	$I_{\mathbf{G}}$	10	mA
Drain Power Dissipation	$P_{\mathrm{D}}$	200	mW
Junction Temperature	$T_j$	125	°C
Storage Temperature Range	$T_{ m stg}$	-55~125	°C

Unit in mm



Weight: 0.13g

#### ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Cut-off Current	IGSS	$V_{GS} = -30V, V_{DS} = 0$		_	-1.0	nA
Gate-Drain Breakdown Voltage	V (BR) GDS	$V_{ m DS} = 0, \; I_{ m G} = -100 \mu { m A}$	-40	_	_	V
Drain Current	I <sub>DSS</sub> (Note)	$V_{DS}=10V, V_{GS}=0$	2.6	_	20	mA
Gate-Source Cut-off Voltage	V <sub>GS</sub> (OFF)	$V_{ m DS} = 10 V, \; I_{ m D} = 0.1 \mu { m A}$	-0.2	_	-1.5	V
Forward Transfer Admittance	Y <sub>fs</sub>	$V_{\mathrm{DS}}$ =10V, $V_{\mathrm{GS}}$ =0, f=1kHz, $I_{\mathrm{DSS}}$ =3mA	8	22	_	mS
Input Capacitance	$\mathrm{c}_{\mathrm{iss}}$	$V_{DS} = 10V, V_{GS} = 0, f = 1MHz$	_	30	_	рF
Reverse Transfer Capacitance	C <sub>rss</sub>	$V_{ m DG} \! = \! 10 V, \; I_{ m D} \! = \! 0, \; f \! = \! 1 MHz$	_	6	_	рF
Noise Figure	NF (1)	$V_{\mathrm{DS}} = 10\mathrm{V}, \ I_{\mathrm{D}} = 1.0\mathrm{mA}, \ \mathrm{R}_{\mathrm{G}} = 1\mathrm{k}\Omega, \ \mathrm{f} = 10\mathrm{Hz}$	_	1.0	10	- dB
	NF (2)	$V_{\mathrm{DS}}$ =10V, $I_{\mathrm{D}}$ =1.0mA, $R_{\mathrm{G}}$ =1k $\Omega$ , $f$ =1k $Hz$	_	0.5	2	ub

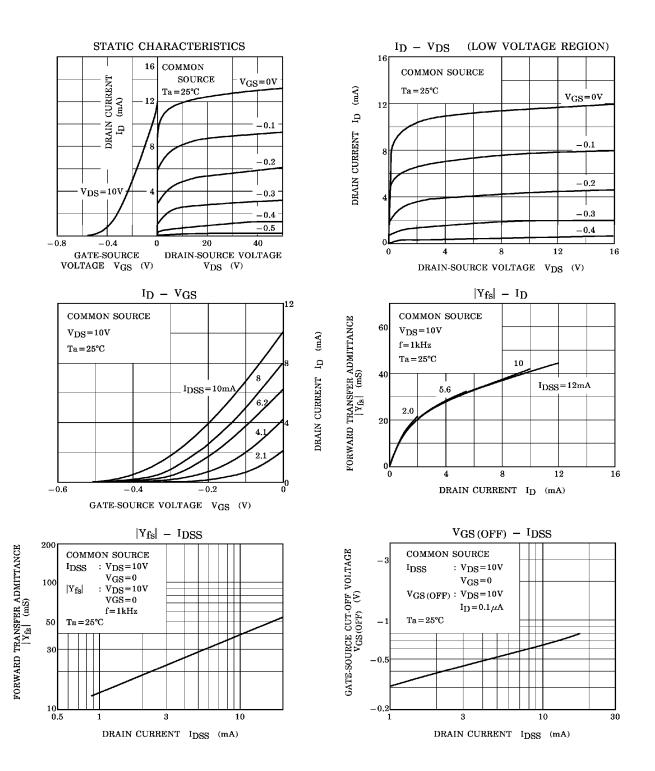
Note: IDSS Classification GR: 2.6~6.5mA, BL: 6.0~12mA, V: 10~20mA

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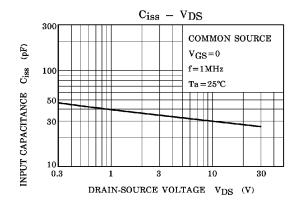


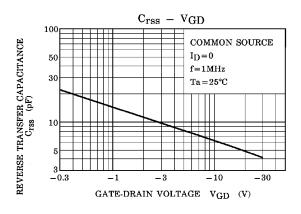
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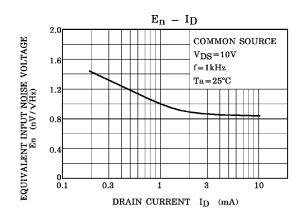
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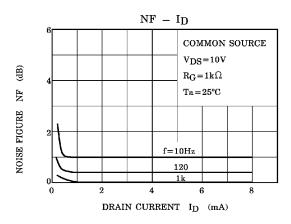
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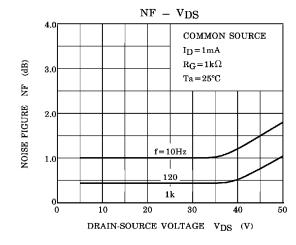
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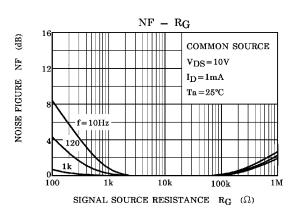






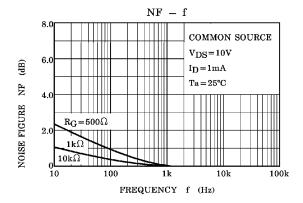


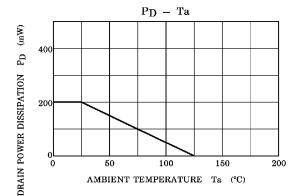


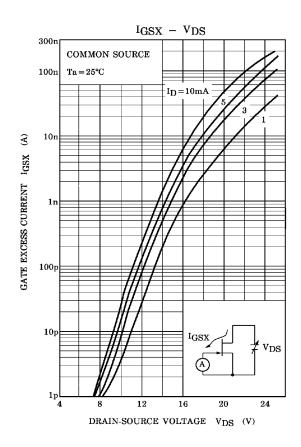


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